

Michael S Shur

List of Publications by Year in descending order

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1,231
papers

39,637
citations

3449

93
h-index

7234

158
g-index

1256
all docs

1256
docs citations

1256
times ranked

18526
citing authors

#	ARTICLE	IF	CITATIONS
1	Accounting for the body effect in the compact modeling of an "extrinsic" MOSFET drain current in the linear and saturation regimes. , 2022, , .		1
2	Graphene-based plasmonic metamaterial for terahertz laser transistors. Nanophotonics, 2022, 11, 1677-1696.	2.9	15
3	LOW-FREQUENCY NOISE IN AlGaIn/GaN HETEROSTRUCTURE FIELD EFFECT TRANSISTORS AND METAL OXIDE SEMICONDUCTOR HETEROSTRUCTURE FIELD EFFECT TRANSISTORS. , 2022, , 419-424.		0
4	Multi-Segment TFT Compact Model for THz Applications. Nanomaterials, 2022, 12, 765.	1.9	2
5	Plasmonic Si CMOS TeraFETs for detection, mixing, and processing sub-THz radiation. , 2022, , .		1
6	Graphene-based plasma-wave devices for terahertz applications. , 2022, , .		0
7	Biomedical applications of terahertz technology. , 2022, , .		7
8	Coulomb drag and plasmonic effects in graphene field-effect transistors enable resonant terahertz detection. Applied Physics Letters, 2022, 120, 111102.	1.5	3
9	Cubic boron nitride as a material for future electron device applications: A comparative analysis. Applied Physics Letters, 2022, 120, .	1.5	10
10	Giant inverse Faraday effect in a plasmonic crystal ring. Optics Express, 2022, 30, 13733.	1.7	1
11	A low-field electron mobility analysis of cubic boron nitride. Solid State Communications, 2022, 352, 114776.	0.9	4
12	Terahertz Plasmonic Technology. IEEE Sensors Journal, 2021, 21, 12752-12763.	2.4	17
13	Pandemic Equation for Describing and Predicting COVID19 Evolution. Journal of Healthcare Informatics Research, 2021, 5, 168-180.	5.3	2
14	Frequency to digital conversion using Si TeraFETs. Optical Engineering, 2021, 60, .	0.5	6
15	Collision dominated, ballistic, and viscous regimes of terahertz plasmonic detection by graphene. Journal of Applied Physics, 2021, 129, .	1.1	21
16	Ultrashort Pulse Detection and Response Time Analysis Using Plasma-Wave Terahertz Field-Effect Transistors. IEEE Transactions on Electron Devices, 2021, 68, 903-910.	1.6	3
17	An improved empirical model for a semiconductor's velocity-field characteristic applied to gallium arsenide. Solid State Communications, 2021, 330, 114240.	0.9	1
18	Modulation characteristics of uncooled graphene photodetectors. Journal of Applied Physics, 2021, 129, .	1.1	10

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19	Heat capacity of nonequilibrium electron-hole plasma in graphene layers and graphene bilayers. <i>Physical Review B</i> , 2021, 103, .	1.1	2
20	Excitonic emission dynamics at cryogenic- and above room temperature in high brightness sub-micron fin LED and Lasers. , 2021, , .		0
21	Coulomb electron drag mechanism of terahertz plasma instability in n+-i-n+ graphene FETs with ballistic injection. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	13
22	Biomedical and Biotechnology Applications of Deep Ultraviolet Light Emitting Diodes. , 2021, , .		2
23	Chip-Scale Droop-Free Fin Light-Emitting Diodes Using Facet-Selective Contacts. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 44663-44672.	4.0	9
24	AI-Powered Terahertz VLSI Testing Technology for Ensuring Hardware Security and Reliability. <i>IEEE Access</i> , 2021, 9, 64499-64509.	2.6	8
25	Theoretical analysis of injection driven thermal light emitters based on graphene encapsulated by hexagonal boron nitride. <i>Optical Materials Express</i> , 2021, 11, 468.	1.6	8
26	Traveling wave TeraFET spectrometer. , 2021, , .		0
27	Line of sight THz detector using TeraFET spectrometers. , 2021, , .		1
28	TeraFET terahertz detectors with spatially non-uniform gate capacitances. <i>Applied Physics Letters</i> , 2021, 119, 161104.	1.5	3
29	Plasmonic Field-Effect Transistors (TeraFETs) for 6G Communications. <i>Sensors</i> , 2021, 21, 7907.	2.1	20
30	Current Driven Plasma Instability in Graphene-FETs with Coulomb Electron Drag. , 2021, , .		0
31	Design and Optimization of TeraFET Spectrometer. , 2021, , .		2
32	Sub-terahertz FET detector with self-assembled Sn-nanowires. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 075102.	1.3	7
33	Sensitivity analysis for an electron transport system: application to the case of wurtzite gallium nitride. <i>Journal of Computational Electronics</i> , 2020, 19, 103-110.	1.3	1
34	TCAD Model for TeraFET Detectors Operating in a Large Dynamic Range. <i>IEEE Transactions on Terahertz Science and Technology</i> , 2020, 10, 15-20.	2.0	8
35	(Keynote) Terahertz Nanoplasmonics Technology: Physics, Applications, and Commercialization. <i>ECS Transactions</i> , 2020, 97, 369-381.	0.3	4
36	p-Diamond, Si, GaN, and InGaAs TeraFETs. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 4858-4865.	1.6	11

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37	Hydrodynamic inverse Faraday effect in a two-dimensional electron liquid. Physical Review B, 2020, 102, .	1.1	5
38	Carbon Nanotube Detectors and Spectrometers for the Terahertz Range. Crystals, 2020, 10, 601.	1.0	3
39	AI Powered THz VLSI Testing Technology. , 2020, , .		5
40	High-brightness lasing at submicrometer enabled by droop-free fin light-emitting diodes (LEDs). Science Advances, 2020, 6, eaba4346.	4.7	30
41	AI Powered THz Testing Technology for Ensuring Hardware Cybersecurity. , 2020, , .		5
42	Electron transport within bulk cubic boron nitride: A Monte Carlo simulation analysis. Journal of Applied Physics, 2020, 128, 185704.	1.1	6
43	Multiple graphene-layer-based heterostructures with van der Waals barrier layers for terahertz superluminescent and laser diodes with lateral/vertical current injection. Semiconductor Science and Technology, 2020, 35, 085023.	1.0	3
44	Plasmonic instabilities in two-dimensional electron channels of variable width. Physical Review B, 2020, 101, .	1.1	18
45	The "Extrinsic" Compact Model of the MOSFET Drain Current Based on a New Interpolation Expression for the Transition Between Linear and Saturation Regimes with a Monotonic Decrease of the Differential Conductance to a Nonzero Value. , 2020, , .		2
46	Plasmonic FET Terahertz Spectrometer. IEEE Access, 2020, 8, 56039-56044.	2.6	15
47	Soft Printable Electrode Coating for Neural Interfaces. ACS Applied Bio Materials, 2020, 3, 4388-4397.	2.3	33
48	Graphene based plasma-wave devices for terahertz applications. Applied Physics Letters, 2020, 116, .	1.5	48
49	Si, SiGe, InP, III-N, and p-diamond FETs and HBTs for sub-terahertz and terahertz applications. , 2020, , .		5
50	Far-infrared photodetectors based on graphene/black-AsP heterostructures. Optics Express, 2020, 28, 2480.	1.7	27
51	Far-infrared and terahertz emitting diodes based on graphene/black-P and graphene/MoS2 heterostructures. Optics Express, 2020, 28, 24136.	1.7	7
52	(Invited) Percolation Carbon Nanotube Thin Film Transistors. ECS Transactions, 2020, 98, 161-171.	0.3	0
53	Describing and Predicting COVID19 Evolution Using Pandemic Equation. , 2020, , .		0
54	Far-infrared photodetection in graphene nanoribbon heterostructures with black-phosphorus base layers. Optical Engineering, 2020, 60, .	0.5	1

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55	TeraFET amplifier detector. , 2020, , .		3
56	P-diamond Plasmonic TeraFET Detector. , 2020, , .		2
57	Carbon nanotube-thin film transistor model for terahertz detectors. , 2020, , .		0
58	Current-driven TeraFET Detector. , 2020, , .		3
59	(Invited) Percolation Carbon Nanotube Thin Film Transistors. ECS Meeting Abstracts, 2020, MA2020-02, 1939-1939.	0.0	0
60	Concepts of infrared and terahertz photodetectors based on vertical graphene van der Waals and HgTe-CdHgTe heterostructures. Opto-electronics Review, 2019, 27, 219-223.	2.4	2
61	An Efficient TCAD Model for TeraFET Detectors. , 2019, , .		4
62	Empirical model for the velocity-field characteristics of semiconductors exhibiting negative differential mobility. Solid State Communications, 2019, 299, 113658.	0.9	4
63	Plasmonic polarization-sensitive detector of terahertz radiation. Journal of Physics: Conference Series, 2019, 1236, 012029.	0.3	1
64	Negative terahertz conductivity and amplification of surface plasmons in graphene“black phosphorus injection laser heterostructures. Physical Review B, 2019, 100, .	1.1	21
65	Modelling of saturation current of an organic field-effect transistor with accounting for contact resistances. IOP Conference Series: Materials Science and Engineering, 2019, 498, 012038.	0.3	1
66	How changes in the crystal temperature and the doping concentration impact upon bulk wurtzite zinc oxide“TM’s electron transport response. MRS Advances, 2019, 4, 2673-2678.	0.5	0
67	Compact Terahertz SPICE/ADS Model. IEEE Transactions on Electron Devices, 2019, 66, 2496-2501.	1.6	16
68	Sub-terahertz testing of millimeter wave Monolithic and very large scale integrated circuits. Solid-State Electronics, 2019, 155, 44-48.	0.8	11
69	Wide band gap semiconductor technology: State-of-the-art. Solid-State Electronics, 2019, 155, 65-75.	0.8	39
70	Negative photoconductivity and hot-carrier bolometric detection of terahertz radiation in graphene-phosphorene hybrid structures. Journal of Applied Physics, 2019, 125, 151608.	1.1	12
71	Optical Pumping of Graphene-Based Heterostructures with Black-Arsenic-Phosphorus Absorbing-Cooling Layer for Terahertz Lasing. , 2019, , .		0
72	Negative Terahertz Conductivity at Vertical Carrier Injection in a Black-Arsenic-Phosphorus“Graphene Heterostructure Integrated With a Light-Emitting Diode. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-9.	1.9	4

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73	Plasmons in Ballistic Nanostructures With Stubs: Transmission Line Approach. IEEE Transactions on Electron Devices, 2019, 66, 126-131.	1.6	11
74	Plasmonic Helicity-Driven Detector of Terahertz Radiation. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800464.	1.2	3
75	Terahertz photoconductive emitter with dielectric-embedded high-aspect-ratio plasmonic grating for operation with low-power optical pumps. AIP Advances, 2019, 9, .	0.6	43
76	Optical pumping in graphene-based terahertz/far-infrared superluminescent and laser heterostructures with graded-gap black-PxAs _{1-x} absorbing-cooling layers. Optical Engineering, 2019, 59, 1.	0.5	8
77	Terahertz plasmonic field effect transistors for imaging applications. , 2019, , .		4
78	THz photonic and plasmonic devices for sensing and communication applications. , 2019, , .		3
79	Terahertz plasmonic detector controlled by phase asymmetry. Optics Express, 2019, 27, 4004.	1.7	18
80	Negative and positive terahertz and infrared photoconductivity in uncooled graphene. Optical Materials Express, 2019, 9, 585.	1.6	24
81	Optical pumping through a black-As absorbing-cooling layer in graphene-based heterostructure: thermo-diffusion model. Optical Materials Express, 2019, 9, 4061.	1.6	9
82	Design of RF to Terahertz and Terahertz to RF Frequency Converters using Variable Width Plasmonic Structures. , 2019, , .		0
83	Graphene-based 2D-heterostructures for terahertz lasers and amplifiers. , 2019, , .		1
84	Plasmonic terahertz emitters with high-aspect ratio metal gratings. , 2019, , .		0
85	Vertical Hot-electron Terahertz Detectors Based on Black-As _{1-x} Px/graphene/black-As _{1-y} Py Heterostructures. Sensors and Materials, 2019, 31, 2271.	0.3	2
86	Comparison of Intersubband Quantum-Well and Interband Graphene-Layer Infrared Photodetectors. IEEE Journal of Quantum Electronics, 2018, 54, 1-8.	1.0	9
87	Device model for pixelless infrared image up-converters based on polycrystalline graphene heterostructures. Journal of Applied Physics, 2018, 123, 014503.	1.1	3
88	Manifestation of plasmonic response in the detection of sub-terahertz radiation by graphene-based devices. Nanotechnology, 2018, 29, 245204.	1.3	18
89	Compact Terahertz SPICE Model: Effects of Drude Inductance and Leakage. IEEE Transactions on Electron Devices, 2018, 65, 5350-5356.	1.6	16
90	p-Diamond as candidate for plasmonic terahertz and far infrared applications. Applied Physics Letters, 2018, 113, .	1.5	21

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91	Electronic Devices Based on Group III Nitrides $\hat{\sim}$. , 2018, , .		1
92	Current-Driven Dyakonov-Shur Instability in Ballistic Nanostructures with a Stub. Physical Review Applied, 2018, 10, .	1.5	13
93	Electrical modulation of terahertz radiation using graphene-phosphorene heterostructures. Semiconductor Science and Technology, 2018, 33, 124010.	1.0	19
94	Real-space-transfer mechanism of negative differential conductivity in gated graphene-phosphorene hybrid structures: Phenomenological heating model. Journal of Applied Physics, 2018, 124, 114501.	1.1	15
95	Silicon and Silicon Germanium Terahertz Electronics. , 2018, , .		2
96	Nanoscale silicon mosfet response to THz radiation for testing VLSI. , 2018, , .		6
97	Interband infrared photodetectors based on HgTe $\hat{\sim}$ CdHgTe quantum-well heterostructures. Optical Materials Express, 2018, 8, 1349.	1.6	13
98	A steady-state and transient analysis of the electron transport that occurs within bulk wurtzite zinc-magnesium-oxide alloys subjected to high-fields. MRS Advances, 2018, 3, 3439-3444.	0.5	1
99	Subterahertz and terahertz sensing of biological objects and chemical agents. , 2018, , .		8
100	Plasmonic heterodimensional resonance for subwavelength imaging. , 2018, , .		4
101	Tunable Stub Plasmonic Structures for Terahertz Detectors and Sources. , 2018, , .		1
102	Plasmonic detectors and sources for THz communication and sensing. , 2018, , .		6
103	Plasmonic shock waves and solitons in a nanoring. Physical Review B, 2017, 95, .	1.1	14
104	Dynamic Conductivity and Two-Dimensional Plasmons in Lateral CNT Networks. International Journal of High Speed Electronics and Systems, 2017, 26, 1740004.	0.3	0
105	Ultimate limits for highest modulation frequency and shortest response time of field effect transistor. Proceedings of SPIE, 2017, , .	0.8	4
106	Detection of terahertz radiation in metamaterials: giant plasmonic ratchet effect (Conference) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 14		
107	Development of Deep UV LEDs and Current Problems in Material and Device Technology. Semiconductors and Semimetals, 2017, 96, 45-83.	0.4	19
108	(Electronics and Photonics Division Award) Physics of Wide Band Gap Semiconductor Devices. ECS Transactions, 2017, 75, 1-8.	0.3	2

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109	Optical polarization control of photo-pumped stimulated emissions at 238 nm from AlGa _N multiple-quantum-well laser structures on AlN substrates. Applied Physics Express, 2017, 10, 012702.	1.1	18
110	Amplified-reflection plasmon instabilities in grating-gate plasmonic crystals. Physical Review B, 2017, 95, .	1.1	42
111	Homodyne phase sensitive terahertz spectrometer. Applied Physics Letters, 2017, 111, .	1.5	19
112	The electron transport that occurs within wurtzite zinc oxide and the application of stress. MRS Advances, 2017, 2, 2627-2632.	0.5	1
113	Plasma Instability of 2D Electrons in a Field Effect Transistor with a Partly Gated Channel. , 2017, , .		0
114	Low-frequency noise in Terahertz plasmonic Field Effect Transistors. , 2017, , .		0
115	Low-frequency noise in quasi-1D TaSe ₃ van der Waals nanowires. , 2017, , .		0
116	Low frequency noise in 2D materials: Graphene and MoS ₂ . , 2017, , .		4
117	Effect of doping on the characteristics of infrared photodetectors based on van der Waals heterostructures with multiple graphene layers. Journal of Applied Physics, 2017, 122, .	1.1	12
118	Terahertz Beam Testing of Millimeter Wave Monolithic Integrated Circuits. IEEE Sensors Journal, 2017, 17, 5487-5491.	2.4	17
119	Low-Frequency Electronic Noise in Quasi-1D TaSe ₃ van der Waals Nanowires. Nano Letters, 2017, 17, 377-383.	4.5	73
120	(Invited) New Approaches for Shrinking the Performance Gap for GaN Power Devices. ECS Transactions, 2017, 80, 147-159.	0.3	1
121	Detection and up-conversion of infrared radiation using van der Waals heterostructures with graphene layers. , 2017, , .		0
122	Heterodyne phase sensitive terahertz spectrometer. , 2017, , .		2
123	Low-frequency noise in terahertz plasmonic field effect transistor sensors. , 2017, , .		0
124	Nonlinear response of infrared photodetectors based on van der Waals heterostructures with graphene layers. Optics Express, 2017, 25, 5536.	1.7	18
125	Color Rendering Metrics: Status, Methods, and Future Development. , 2017, , 799-827.		2
126	Electron Transport Within III-V Nitride Semiconductors. Springer Handbooks, 2017, , 1-1.	0.3	9

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127	Subpicosecond Nonlinear Plasmonic Response Probed by Femtosecond Optical Pulses. , 2017, , .		2
128	(Invited) New Approaches for Shrinking the Performance Gap for GaN Power Devices. ECS Meeting Abstracts, 2017, , .	0.0	0
129	TERAHERTZ AND INFRARED PHOTODETECTORS BASED ON VERTICAL GRAPHENE VAN DER WAALS HETEROSTRUCTURES: CONCEPTS, FEATURES OF OPERATION AND CHARACTERISTICS. , 2017, , 159-167.		0
130	Selective Gas Sensor Using Porous Silicon. Sensor Letters, 2016, 14, 588-591.	0.4	11
131	Transition from capacitive coupling to direct charge transfer in asymmetric terahertz plasmonic assemblies. Optics Letters, 2016, 41, 5333.	1.7	77
132	Plasmonic Enhancement of Terahertz Devices Efficiency. International Journal of High Speed Electronics and Systems, 2016, 25, 1640019.	0.3	0
133	Temperature-dependent efficiency droop in AlGaIn epitaxial layers and quantum wells. AIP Advances, 2016, 6, .	0.6	10
134	Resonant plasmonic terahertz detection in graphene split-gate field-effect transistors with lateral p-n junctions. Journal Physics D: Applied Physics, 2016, 49, 315103.	1.3	27
135	Two-dimensional plasmons in lateral carbon nanotube network structures and their effect on the terahertz radiation detection. Journal of Applied Physics, 2016, 120, 044501.	1.1	18
136	High-Speed Room Temperature Terahertz Detectors Based on InP Double Heterojunction Bipolar Transistors. International Journal of High Speed Electronics and Systems, 2016, 25, 1640011.	0.3	13
137	Subpicosecond Nonlinear Plasmonic Response Probed by Femtosecond Optical Pulses. International Journal of High Speed Electronics and Systems, 2016, 25, 1640003.	0.3	3
138	Plasma Instability of 2D Electrons in a Field Effect Transistor with a Partly Gated Channel. International Journal of High Speed Electronics and Systems, 2016, 25, 1640015.	0.3	12
139	Physics of ultrahigh speed electronic devices. , 2016, , .		0
140	Photomodification of carrier lifetime and diffusivity in AlGaIn epitaxial layers. Current Applied Physics, 2016, 16, 633-637.	1.1	2
141	Dependence of radiative and nonradiative recombination on carrier density and Al content in thick AlGaIn epilayers. Journal Physics D: Applied Physics, 2016, 49, 145110.	1.3	17
142	Graphene-based van der Waals heterostructures for emission and detection of terahertz radiation. Proceedings of SPIE, 2016, , .	0.8	2
143	(Invited) The Compact Models and Parameter Extraction for Thin Film Transistors. ECS Transactions, 2016, 75, 171-178.	0.3	1
144	Terahertz compact SPICE model. , 2016, , .		1

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145	New optical gating technique for detection of electric field waveforms with subpicosecond resolution. <i>Optics Express</i> , 2016, 24, 12730.	1.7	6
146	Breakdown current density in h-BN-capped quasi-1D TaSe ₃ metallic nanowires: prospects of interconnect applications. <i>Nanoscale</i> , 2016, 8, 15774-15782.	2.8	79
147	THz pulse detection by photoconductive plasmonic high electron mobility transistor with enhanced sensitivity. , 2016, , .		4
148	Silicon-on-Insulator Photoimpedance Sensor Using Capacitance Dispersion. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 3236-3240.	1.6	3
149	Scanning near-field optical microscopy of AlGaN epitaxial layers. <i>Proceedings of SPIE</i> , 2016, , .	0.8	0
150	Current-driven plasmonic boom instability in three-dimensional gated periodic ballistic nanostructures. <i>Physical Review B</i> , 2016, 93, .	1.1	48
151	Models for plasmonic THz detectors based on graphene split-gate FETs with lateral p-n junctions. , 2016, , .		0
152	Plasma shock waves excited by THz radiation. , 2016, , .		0
153	(Invited) Physics of GaN High Electron Mobility Transistors. <i>ECS Transactions</i> , 2016, 75, 69-76.	0.3	1
154	Plasmonic response of partially gated field effect transistors. <i>Proceedings of SPIE</i> , 2016, , .	0.8	0
155	Novel ultrasensitive plasmonic detector of terahertz pulses enhanced by femtosecond optical pulses. <i>Proceedings of SPIE</i> , 2016, , .	0.8	0
156	A sensitivity analysis on the electron transport within zinc oxide and its device implications. <i>MRS Advances</i> , 2016, 1, 2777-2782.	0.5	2
157	Plasmonic properties of asymmetric dual grating gate plasmonic crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 671-675.	0.7	9
158	Recent developments in terahertz sensing technology. <i>Proceedings of SPIE</i> , 2016, , .	0.8	2
159	Tunable, Room Temperature CMOS-Compatible THz Emitters Based on Nonlinear Mixing in Microdisk Resonators. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2016, 37, 230-242.	1.2	11
160	Acoustoelectric effects in reflection of leaky-wave-radiated bulk acoustic waves from piezoelectric crystal-conductive liquid interface. <i>Ultrasonics</i> , 2016, 64, 196-199.	2.1	2
161	Color Rendering Metrics: Status, Methods, and Future Development. , 2016, , 1-29.		2
162	Contactless Monitoring of Conductivity Changes in Vanadium Pentoxide Xerogel Layers Using Surface Acoustic Waves. <i>Physics Procedia</i> , 2015, 70, 135-138.	1.2	0

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163	Is zinc oxide a potential material for future high-power and high-frequency electron device applications?. Materials Research Society Symposia Proceedings, 2015, 1805, 1.	0.1	3
164	Heterodimensional transistor technology for attojoule electronics. , 2015, , .		0
165	Terahertz Sensing Technology. Selected Topics in Electornics and Systems, 2015, , 1-29.	0.2	0
166	Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. Selected Topics in Electornics and Systems, 2015, , 31-53.	0.2	1
167	Resonant plasmonic terahertz detection in vertical graphene-base hot-electron transistors. Journal of Applied Physics, 2015, 118, .	1.1	16
168	Spectral dependence of carrier lifetime in high aluminum content AlGa _N epitaxial layers. Journal of Applied Physics, 2015, 118, 085705.	1.1	8
169	Negative terahertz conductivity in remotely doped graphene bilayer heterostructures. Journal of Applied Physics, 2015, 118, .	1.1	4
170	Suppression of 1/f noise in near-ballistic h-BN-graphene-h-BN heterostructure field-effect transistors. Applied Physics Letters, 2015, 107, .	1.5	85
171	InP Double Heterojunction Bipolar Transistor for broadband terahertz detection and imaging systems. Journal of Physics: Conference Series, 2015, 647, 012036.	0.3	8
172	Efficiency droop and carrier transport in AlGa _N epilayers and heterostructures. Physica Status Solidi (B): Basic Research, 2015, 252, 961-964.	0.7	3
173	Graphene active plasmonics for terahertz device applications. , 2015, , .		0
174	Electron transport and electron energy distributions within the wurtzite and zinc-blende phases of indium nitride: Response to the application of a constant and uniform electric field. Journal of Applied Physics, 2015, 117, 125705.	1.1	15
175	(Invited) Plasmonic Terahertz Detectors. ECS Transactions, 2015, 66, 139-144.	0.3	0
176	Terahertz electronics for sensing and imaging applications. , 2015, , .		4
177	(Invited) Power Loss Reduction in Perforated-Channel HFET Switches. ECS Transactions, 2015, 66, 179-183.	0.3	0
178	Low-noise near-ballistic BN-graphene-BN heterostructure field-effect transistors for energy efficient electronic applications. , 2015, , .		0
179	Vertical hot-electron graphene-base transistors as resonant plasmonic terahertz detectors. , 2015, , .		0
180	Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. International Journal of High Speed Electronics and Systems, 2015, 24, 1550002.	0.3	6

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181	Nonradiative Recombination, Carrier Localization, and Emission Efficiency of AlGa _N Epilayers with Different Al Content. <i>Journal of Electronic Materials</i> , 2015, 44, 4706-4709.	1.0	5
182	InP double heterojunction bipolar transistor for detection above 1 THz. , 2015, , .		1
183	High-temperature performance of MoS ₂ thin-film transistors: Direct current and pulse current-voltage characteristics. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	34
184	Graphene Active Plasmonics for New Types of Terahertz Lasers. , 2015, , .		1
185	Selective chemical vapor sensing with few-layer MoS ₂ thin-film transistors: Comparison with graphene devices. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	112
186	Helicity-Driven Ratchet Effect Enhanced by Plasmons. <i>Physical Review Letters</i> , 2015, 114, 246601.	2.9	47
187	Ultimate response time of high electron mobility transistors. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	27
188	Novel AlInN/GaN integrated circuits operating up to 500Å°C. <i>Solid-State Electronics</i> , 2015, 113, 22-27.	0.8	17
189	Response of plasmonic terahertz detectors to amplitude modulated signals. <i>Solid-State Electronics</i> , 2015, 111, 76-79.	0.8	10
190	A 2015 perspective on the nature of the steady-state and transient electron transport within the wurtzite phases of gallium nitride, aluminum nitride, indium nitride, and zinc oxide: a critical and retrospective review. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 4475-4512.	1.1	33
191	Acoustoelectric investigation of V ₂ O ₅ ·nH ₂ O thin film transition from wet gel to xerogel. <i>Journal of Non-Crystalline Solids</i> , 2015, 425, 24-27.	1.5	1
192	Low-temperature redistribution of non-thermalized carriers and its effect on efficiency droop in AlGa _N epilayers. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 275105.	1.3	10
193	Acousto-Optic Diffraction by Shear Horizontal Surface Acoustic Waves in 36Å° Rotated Y-Cut X-Propagation Lithium Tantalate. <i>Acta Physica Polonica A</i> , 2015, 127, 52-54.	0.2	1
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